

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A photoresist composition comprising:
a base material resin component (A) which exhibits changed alkali solubility under the
action of acid;
an acid generator component (B) which generates the acid on exposure to radiation; and
at least one nitrogen-containing compound (D) selected from tertiary alkanolamines
containing 6 to 12 carbon atoms, wherein
the base material resin component (A) is a polymer compound comprising:
an alkali soluble group (i), wherein
at least one hydrogen atom of a hydroxyl group in the alkali soluble group (i) is
protected by an acid dissociable, dissolution inhibiting group (ii) represented by the
general formula (1):
$$\text{---CH}_2\text{-O-R (1)}$$

(wherein R represents an organic group containing no more than 20 carbon atoms
and at least one hydrophilic group); and
~~wherein the polymer compound exhibits changed alkali solubility under the action~~
~~of acid.~~
2. (Currently amended) A ~~polymer compound~~ photoresist composition according
to claim 1, wherein the alkali soluble group (i) is selected from the group consisting of an
alcoholic hydroxyl group, a phenolic hydroxyl group, and a carboxyl group.
3. (Currently amended) A ~~polymer compound~~ photoresist composition according
to claim 2, wherein a carbon atom adjacent to the carbon atom connected to the alcoholic
hydroxyl group is bonded to at least one fluorine atom.
4. (Currently amended) A ~~polymer compound~~ photoresist composition according
to claim 1, wherein the hydrophilic group is selected from the group consisting of a carbonyl
group, an ester group, an alcoholic hydroxyl group, an ether group, an imino group, and an amino
group.
5. (Canceled)

6. **(Currently amended)** A resist pattern formation method comprising:
- forming a photoresist film on a substrate using the photoresist composition according to claim [[5]] 1;
 - exposing the photoresist film; and
 - developing the exposed photoresist film to form a resist pattern.